

30V Half Bridge Dual N-Channel Super Trench Power MOSFET

**Description**

The HM35SDN03D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . It includes two specialized MOSFETs in a dual Power DFN5x6 package.

**General Features**

**Q1 "High Side" MOSFET**

●  $V_{DS} = 30V, I_D = 35A$

$R_{DS(ON)} < 7m\Omega @ V_{GS} = 10V$

$R_{DS(ON)} < 12m\Omega @ V_{GS} = 4.5V$

● Excellent gate charge x  $R_{DS(on)}$  product(FOM)

● Very low on-resistance  $R_{DS(on)}$

● 150 °C operating temperature

● Pb free terminal plating

● RoHS compliant

● Halogen free

**Application**

● Compact DC/DC converter applications

**100% UIS TESTED!**

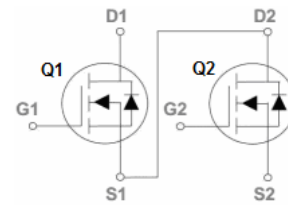
**100% ΔVds TESTED!**

**Q2 "Low Side" MOSFET**

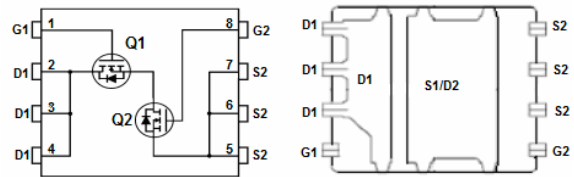
$V_{DS} = 30V, I_D = 35A$

$R_{DS(ON)} < 7m\Omega @ V_{GS} = 10V$

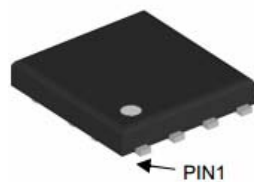
$R_{DS(ON)} < 12m\Omega @ V_{GS} = 4.5V$



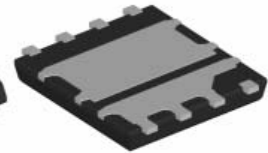
Schematic Diagram



pin assignment



Top View



Bottom View

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM35SDN03D	HM35SDN03D	DFN5X6-8L	330mm	12mm	5000 units

**Absolute Maximum Ratings ( $T_C=25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Q1	Q2	Unit
Drain-Source Voltage	$V_{DS}$	30	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Drain Current-Continuous (Note 2)	$I_D$	$T_C=25^\circ C$	35	A
		$T_C=100^\circ C$	24.5	A
Drain Current -Pulsed (Note 1)	$I_{DM}$	105	105	A
Power Dissipation	$P_D$	30	80	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	-55 To 150	$^\circ C$

**Thermal Characteristic**

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Case (Note 2) (Q1)	$R_{\theta JC}$	3.3	4.2	$^\circ C/W$
Thermal Resistance, Junction-to-Case (Note 2) (Q2)	$R_{\theta JC}$	1.2	1.6	$^\circ C/W$

**Q1 Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	-	5.5	7	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	-	7.8	12	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =15A		30	-	S
<b>Dynamic Characteristics</b> (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1.0MHz	-	822	-	PF
Output Capacitance	C <sub>oss</sub>		-	344	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	15.3	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =15A V <sub>GS</sub> =10V, R <sub>G</sub> =1.6Ω	-	6.5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	2.5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	17	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	2.5	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =15A, V <sub>GS</sub> =10V	-	15	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.9		nC
Gate-Drain Charge	Q <sub>gd</sub>		-	2.1		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-		1.2	V
Diode Forward Current	I <sub>S</sub>		-	-	35	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>	-	11	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100A/μs (Note3)	-	19	-	nC

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=15V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω

Q1 Typical Electrical and Thermal Characteristics

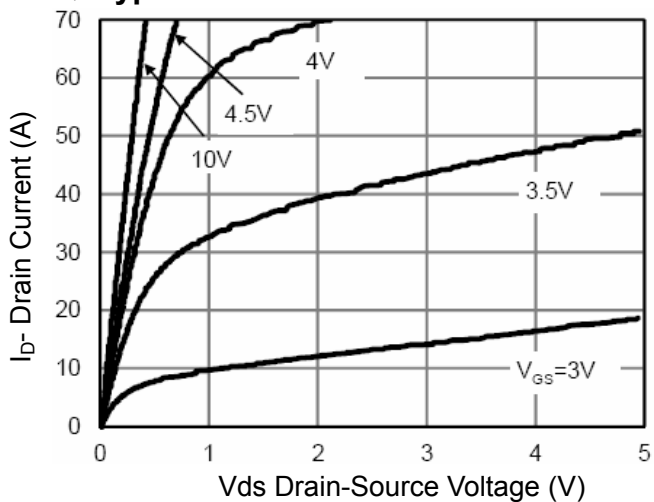


Figure 1 Output Characteristics

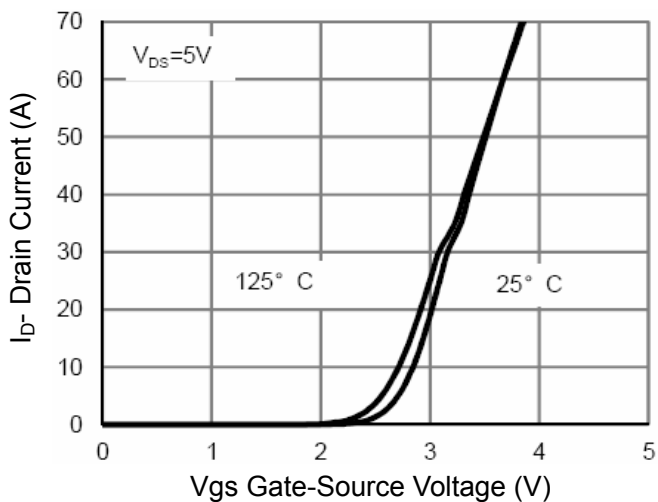


Figure 2 Transfer Characteristics

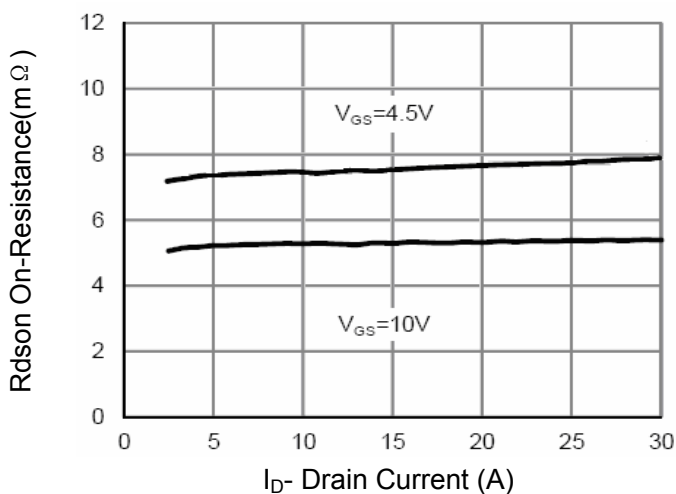


Figure 3  $R_{Dson}$ - Drain Current

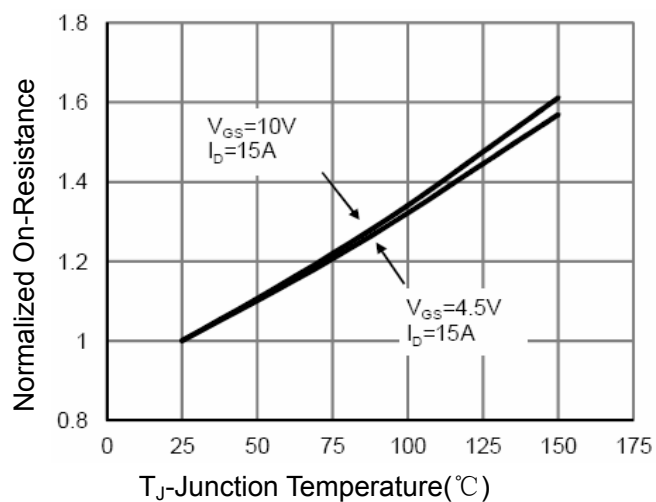


Figure 4  $R_{Dson}$ -Junction Temperature

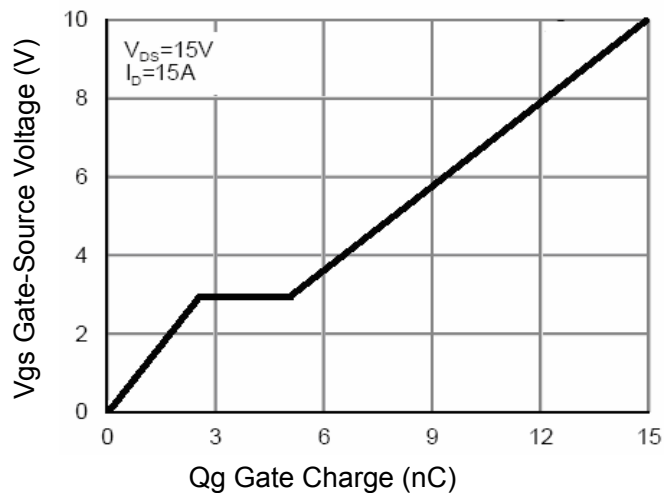


Figure 5 Gate Charge

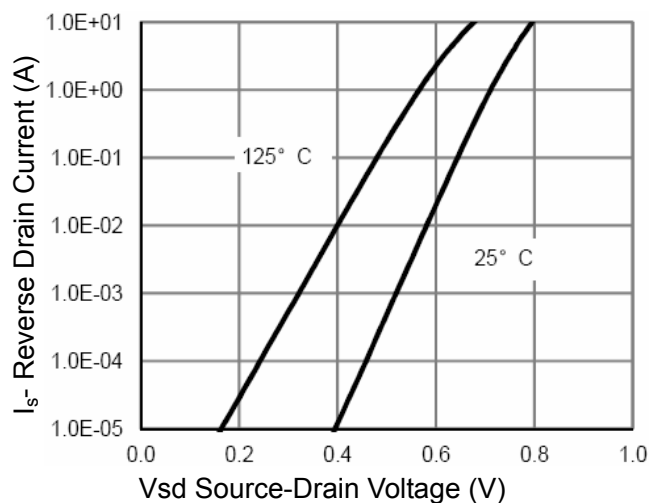


Figure 6 Source- Drain Diode Forward

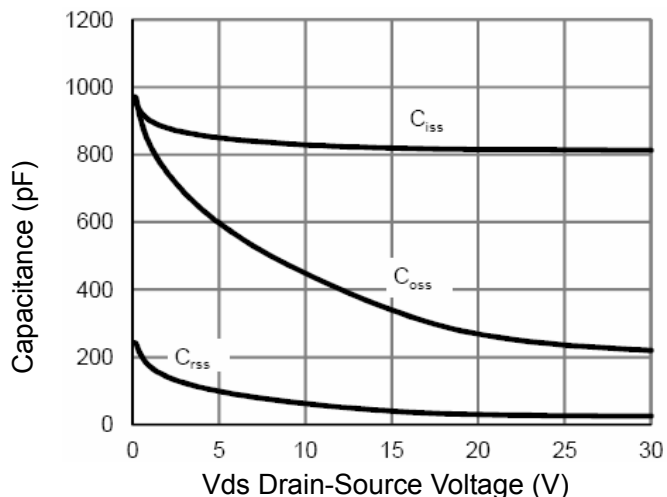


Figure 7 Capacitance vs Vds

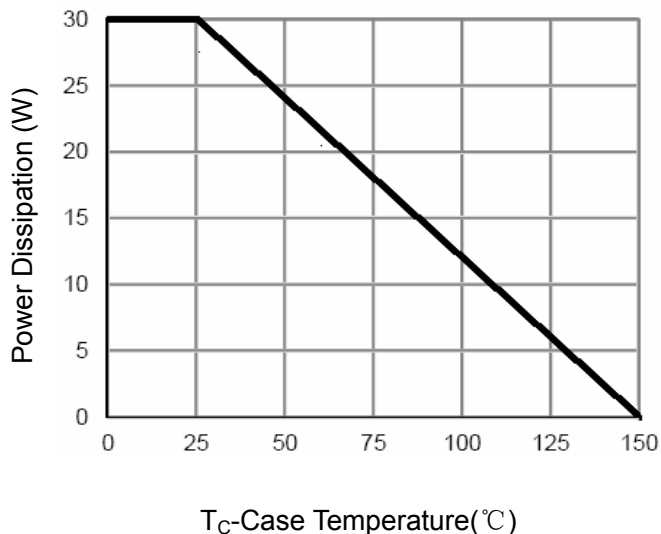


Figure 9 Power De-rating

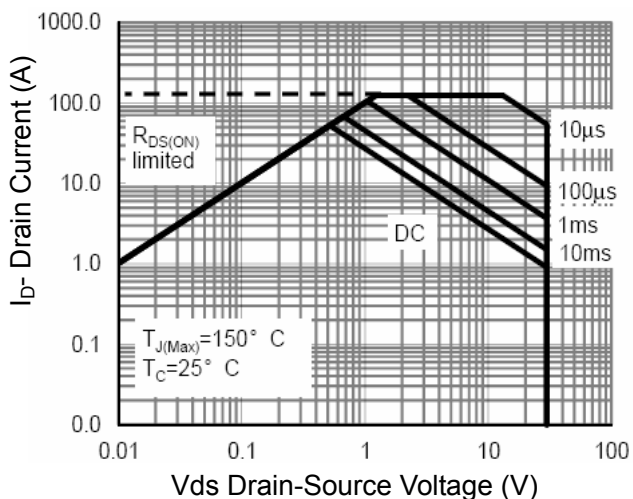


Figure 8 Safe Operation Area

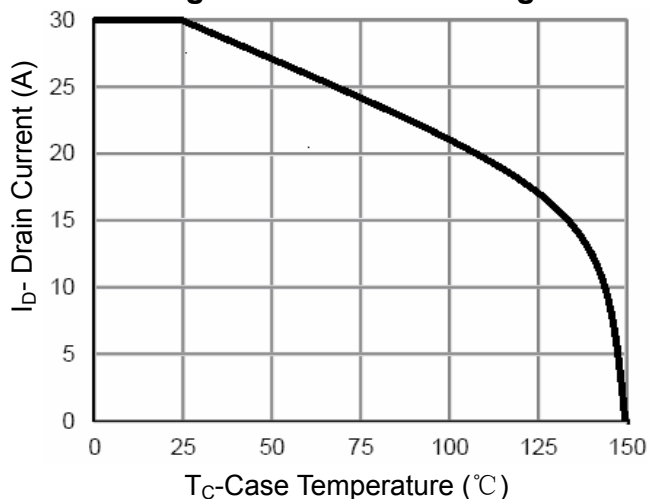


Figure 10 Current De-rating

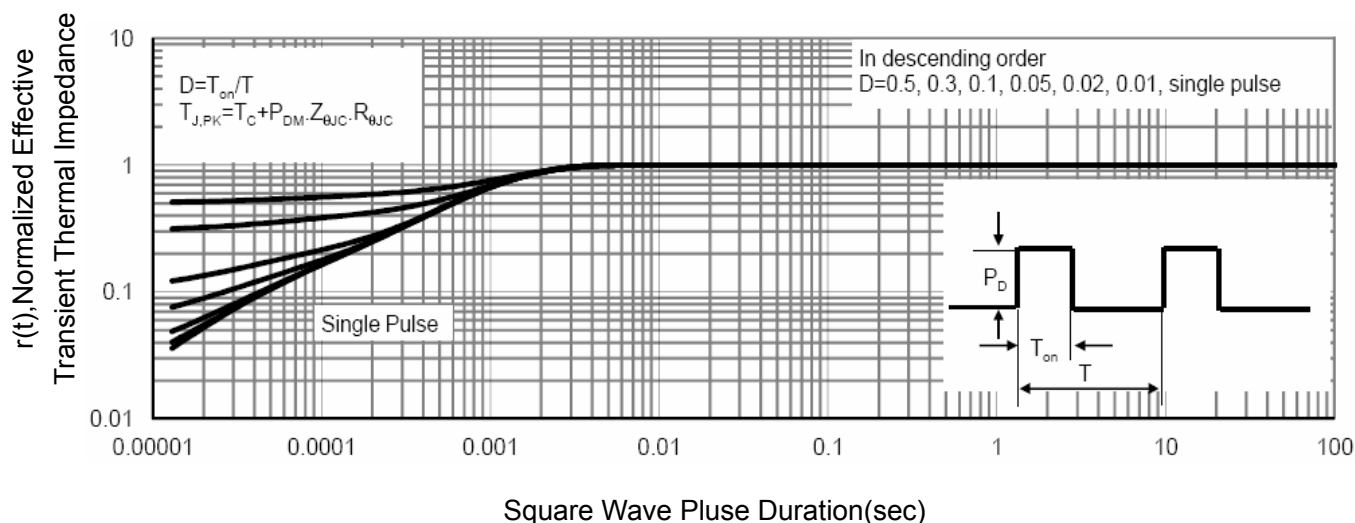


Figure 11 Normalized Maximum Transient Thermal Impedance

**Q2 Electrical Characteristics (TC=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=50A$	-	5.5	7	m $\Omega$
		$V_{GS}=4.5V, I_D=50A$	-	7.8	12	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=50A$		65	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	3370	-	PF
Output Capacitance	$C_{oss}$		-	902	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	60	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=50A$ $V_{GS}=10V, R_G=1.6\Omega$	-	7	-	nS
Turn-on Rise Time	$t_r$		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	32	-	nS
Turn-Off Fall Time	$t_f$		-	9	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=50A,$ $V_{GS}=10V$	-	55	-	nC
Gate-Source Charge	$Q_{gs}$		-	9		nC
Gate-Drain Charge	$Q_{gd}$		-	8.5		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=50A$	-		1.2	V
Diode Forward Current	$I_S$		-	-	35	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ C, I_F = I_S$ $di/dt = 500A/\mu s$ (Note 3)	-	20	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	50	-	nC

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^\circ C, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25\Omega$

Q2 Typical Electrical and Thermal Characteristics

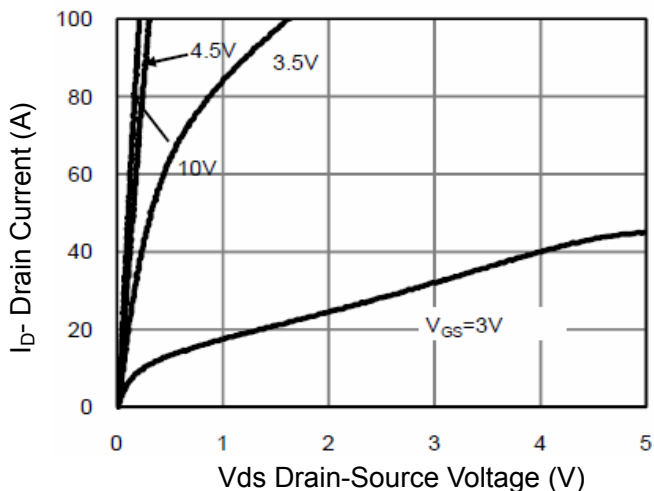


Figure 1 Output Characteristics

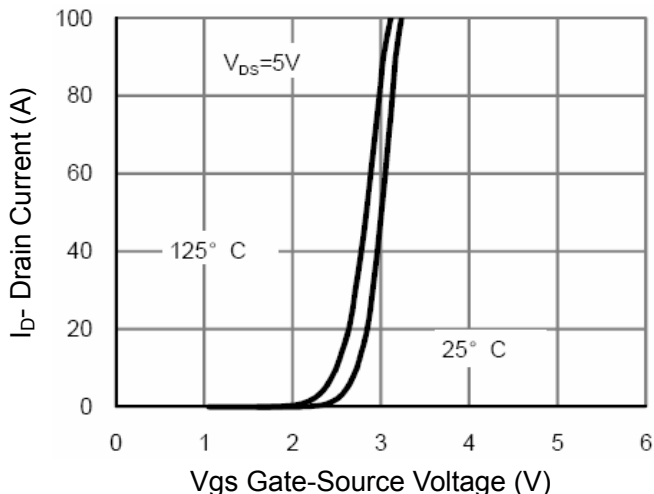


Figure 2 Transfer Characteristics

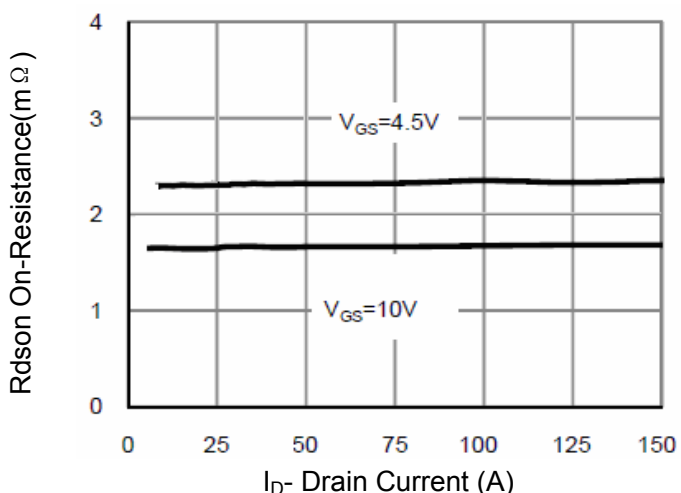


Figure 3 Rdson- Drain Current

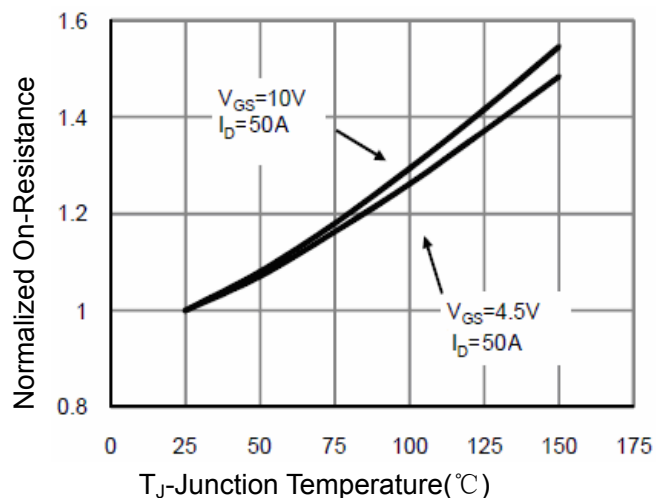


Figure 4 Rdson-Junction Temperature

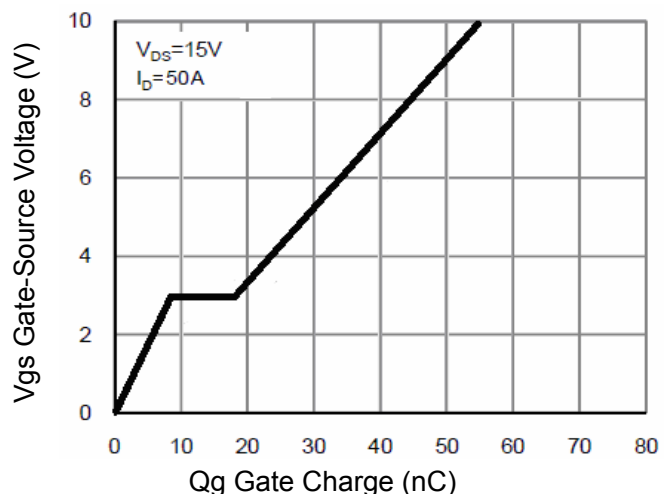


Figure 5 Gate Charge

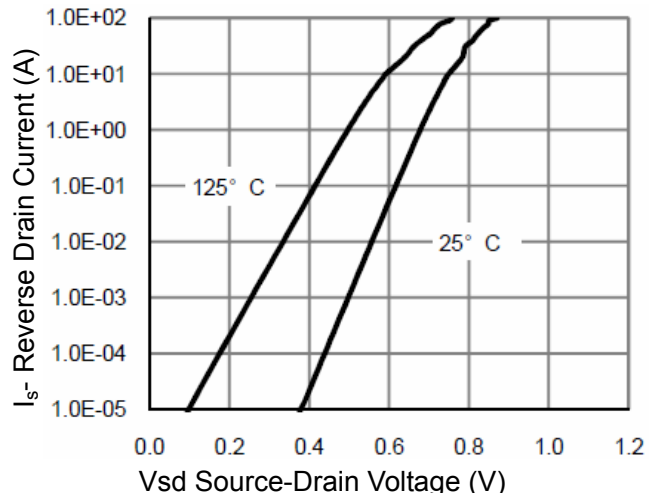


Figure 6 Source- Drain Diode Forward

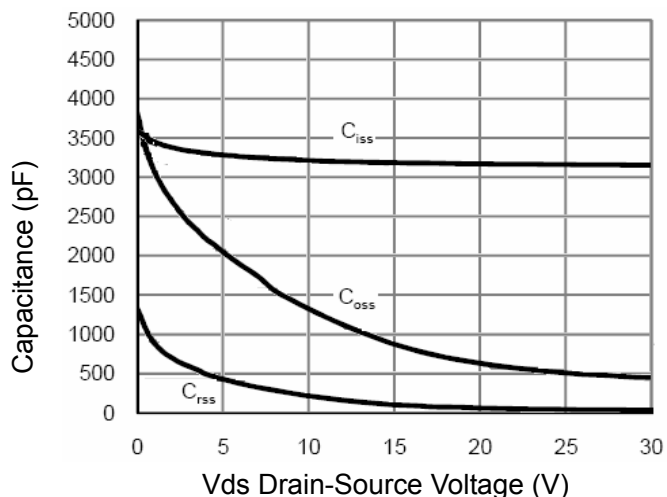


Figure 7 Capacitance vs Vds

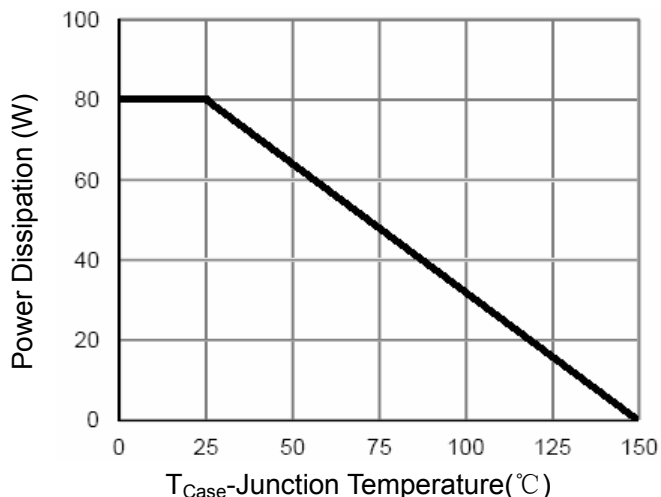


Figure 9 Power De-rating

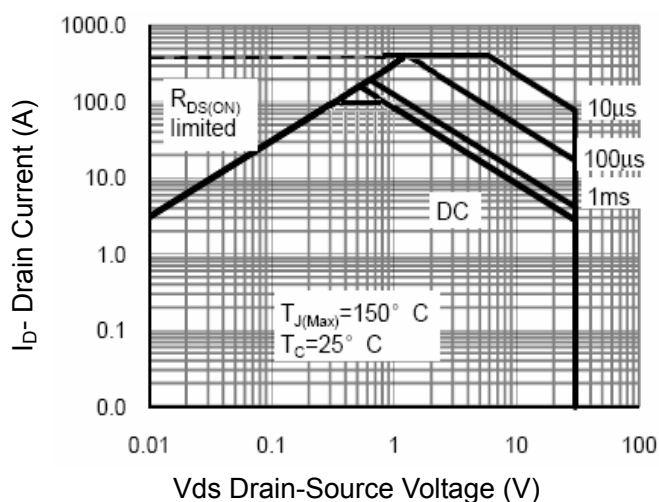


Figure 8 Safe Operation Area

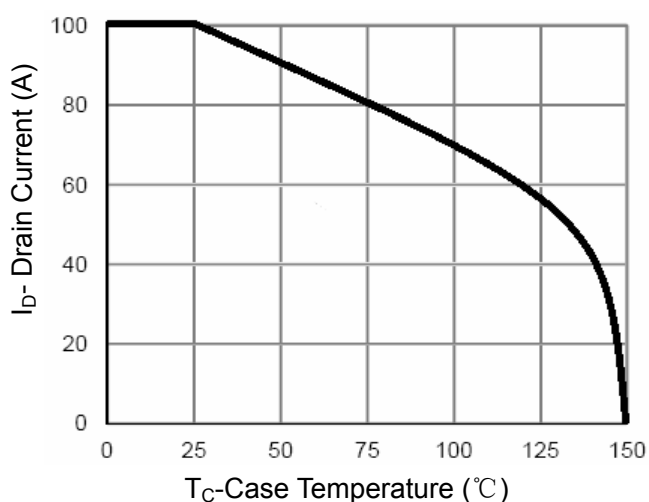


Figure 10 Current De-rating

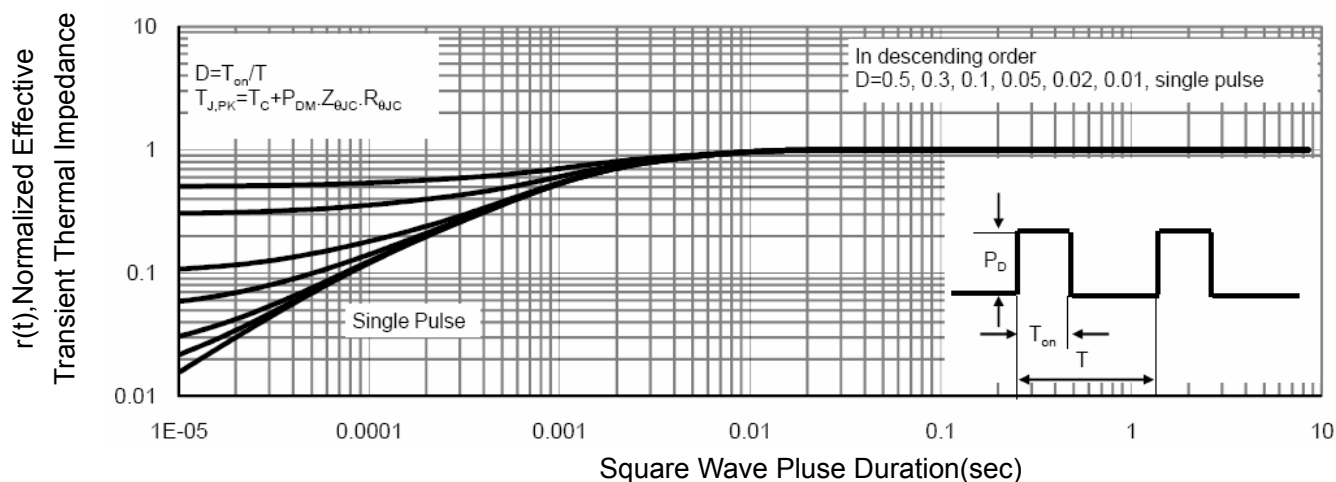
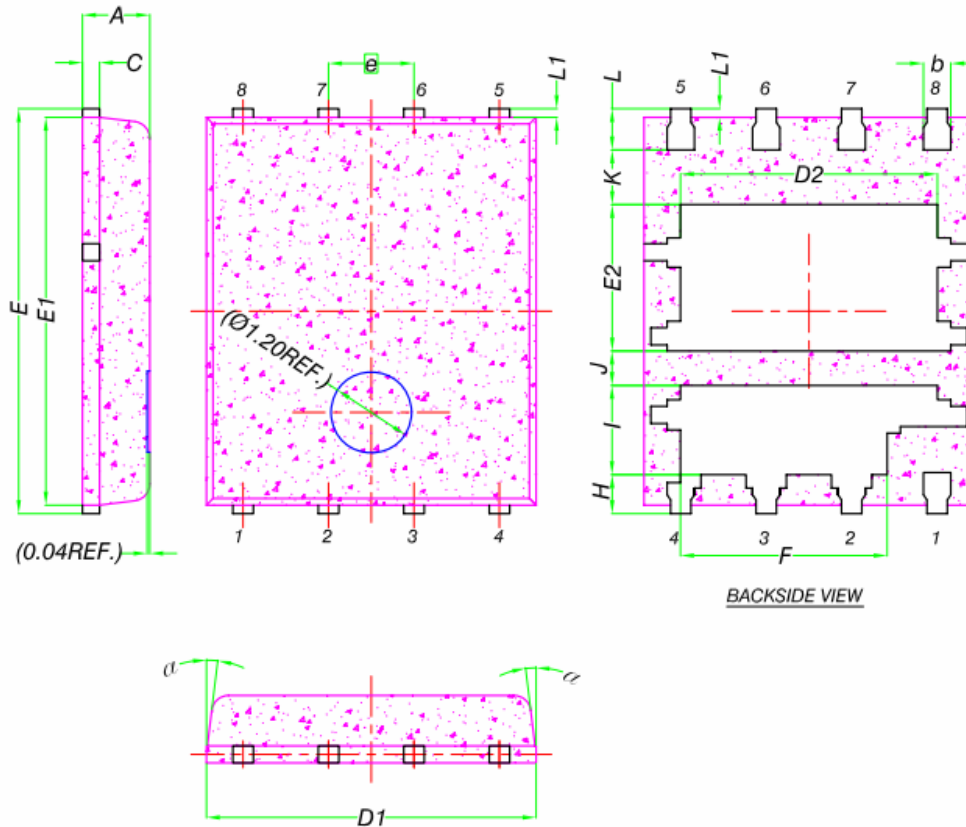


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	2.02	2.17	2.32
$e$	1.27 BSC		
F	2.87	3.07	3.22
H	0.48	0.58	0.68
I	1.22	1.32	1.42
J	0.40	0.50	0.60
K	0.50	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
$\alpha$	0°	-	12°

